

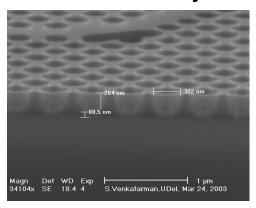
ICP Etching System For Research & Development MODEL RIE-101iPH





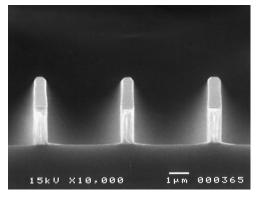
Examples of Etching Process

-Si / InP Photonic Crystals-



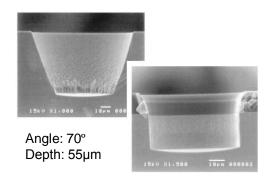
Width:320nm Depth:264nm

—Al Fine Pattern Etch—



Width: 500nm Depth: 100µm

—GaAs Etch—



Etch Rate: >1um/min

Angle: 89° Depth: 24um



The SAMCO RIE-101iPH is a load-locked type inductively coupled (ICP) etching system. The system designed for R&D customers who require a flexible system capable of etching a large number of materials in one system.

The system features SAMCO's proprietary Tornado ICP® configuration that efficiently generates a highly uniform, high density plasma. This enables the system to achieve precise pattern etching with high selectivity between the mask and etch materials with superior uniformity.

Features

- Proprietary Tornado ICP® coil delivers highly uniform, high density plasma.
- Stainless steel chamber allows easy cleaning and prevents corrosion.
- Advanced chamber design allows advanced etching of a large range of materials
- Control of the sample temperature by electro static chuck
- Multiple spare ports allows more analytical instruments to be attached (options).

Applications

- Anisotropic etching of silicon based films.
- Etching of metal films
- •Etching of GaN, GaAs, InP and other compound semiconductor films
- Fabrication of waveguide devices
- •High speed etching of Al₂O₃, SiO₂

Utility Requirements			
Power	•AC200V, Ø3, 60A		
Cooling Water	•Above 2L/min for the electrode •Above 5L/min for the chamber		
Exhaust Ducts	•Main body •Gas box		
Gas Exhaust	•NW25 from two rotary pumps		
Process Gases	•0.1MPa(G)		
Compressed Air	•0.5~0.7MPa(G)		
Nitrogen Supply	•0.1MPa(G) for chambers •0.05~0.1MPa(G) for rotary pumps		

System Specifications				
Process Chamber	Stainless steel, 309.5mm diameter 40mm diameter view port 9 spare ports for analytical instruments (# of ports is dependent on specification)			
Sample	•4" sample stage			
Electrodes	ICP Electrode: •Tornado Coil Electrode® Lower Electrode: •Stainless steel, Ø106mm reactor			
RF Power	ICP: •13.56MHz, 1kW, crystal oscillation •Auto matching BIAS: •13.56MHz, 300W, crystal oscillation •Auto matching			
Load-lock Chamber	•Aluminum, 451(W) x 308(D) x 146 (H) •Linear motion vacuum robot			
Vacuum System	Process Vacuum Line: •Compound turbo molecular pump (800L/sec) •Fomblin rotary pump (413L/min) •Variable conductance motorized gate valve Load-lock / Roughing Line: •SA-M rotary pump (413L/min)			
Gauges	Process Chamber: •Diaphragm gauge, 1.33 ~ 1.6x10 ⁻² •lonization gauge, 1.3x10 ⁻¹ ~ 1x10 ⁻⁵ Load Lock Chamber: •Pirani gauge, 3x10 ⁻³ ~ 4x10 ⁻¹			
Gas Lines	•Four mass flow controllers (standard)			
Operation	*Fully automatic "auto" operation *Manual operation mode *Recipe storage * 100 Recipes, 10 steps per recipe *Safety interlocks to prevent errors in operation.			
	Options			
BIAS Power	•300W → 500W			
Pumps	•Rotary pump → dry pump •TMP for Ga etching			
Circulators	Room temperature High temperature (for In containing materials)			
Gas Lines	•Extra lines (up to 8 possible)			











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